

<b>Notice of References Cited</b>	Application/Control No. 10/566,522		Applicant(s)/Patent Under Reexamination JIN ET AL.	
	Examiner JAMI M. VALENTINE		Art Unit 2894	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2005/0111256	05-2005	Bednorz et al.	365/177
*	B	US-7,099,141	08-2006	Kaufman et al.	361/311
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
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	R					
	S					
	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Beck et al.("Reproducible switching effect in thin oxide films for memory applications" Applied Physics Letters, Vol. 77, No. 1, July 2000, page 139)
	V	Watanabe et al ("Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO3 single crystals" Applied Physics Letters, Vol. 78, No. 23, June 2001 page 3738)
	W	Rossel et al ("Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, September 2001, page 2892)
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.